

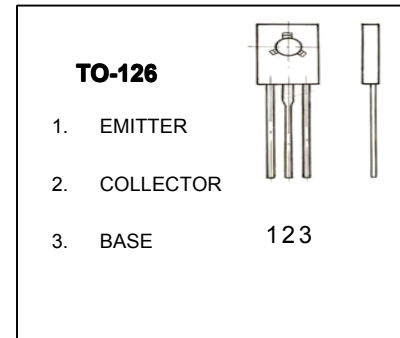


DONGGUAN NANJING ELECTRONICS LTD.,  
**TO-126 Plastic-Encapsulate Transistors**

**D882** TRANSISTOR (NPN)

FEATURES

Power Dissipation



**MAXIMUM RATINGS** (TA=25°C unless otherwise noted)

Symbol (符号)	Parameter (参数名称)	Value (额定值)	Units (单位)
<b>VCBO</b>	Collector-Base Voltage (集电极-基极电压)	40	V
<b>VCEO</b>	Collector-Emitter Voltage (集电极-发射极电压)	30	V
<b>VEBO</b>	Emitter-Base Voltage (发射极-基极电压)	6	V
<b>IC</b>	Collector Current -Continuous (集电极电流)	3.0	A
<b>PC</b>	Collector Power Dissipation (耗散功率)	1.25	W
<b>Tj</b>	Junction Temperature (结温)	150	°C
<b>Tstg</b>	Storage Temperature (储存温度)	-55-150	°C

**ELECTRICAL CHARACTERISTICS** (Tamb=25°C unless otherwise specified)

Parameter (参数名称)	Symbol (符号)	Test conditions (测试条件)	MIN (最小值)	TYP (典型值)	MAX (最大值)	UNIT (单位)
Collector-base breakdown voltage 集电极-基极击穿电压	V(BR)CBO	IC= 100μA, IE=0	40			V
Collector-emitter breakdown voltage 集电极-发射极击穿电压	V(BR)CEO	IC= 1mA, IB=0	30			V
Emitter-base breakdown voltage 发射极-基极击穿电压	V(BR)EBO	IE=100μA, IC=0	6			V
Collector cut-off current 集电极-基极截止电流	ICBO	VCE=30 V, IE=0			1	μ A
Collector cut-off current 集电极-发射极截止电流	ICEO	VCE=25V, IB=0			10	μ A
Emitter cut-off current 发射极-基极截止电流	IEBO	VEB=5V, IC=0			1	μ A
DC current gain 直流电流增益	hFE	VCE=2V, IC= 1A	100		400	
DC current gain 直流电流增益	hFE	VCE=2V, IC= 20mA	80			
Collector-emitter saturation voltage 集电极-发射极饱和电压	VCE(sat)	IC=2A, IB=200mA			0.5	V
Base-emitter saturation voltage 发射极-基极饱和电压	VBE(sat)	IC=2A, IB=200mA			1.2	V

**CLASSIFICATION OF hFE**

Range	100-200	200-300	300-400	

# Typical Characteristics

# D882

